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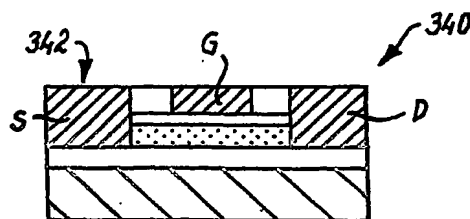
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(54) Title: A TRANSISTOR DEVICE WITH METALLIC ELECTRODES AND A METHOD FOR USE IN FORMING SUCH A
DEVICE



(57) Abstract: A transistor device having a metallic source electrode, a metallic drain electrode, a metallic gate electrode and a channel in a deposited semiconductor material, the transistor device comprising: a first layer comprising the metallic gate electrode, a first metal portion of the metallic source electrode and a first metal portion of the metallic drain electrode; a second layer comprising a second metal portion of the metallic source electrode, a second metal portion of the metallic drain electrode, the deposited semiconductor material and dielectric material between the semiconductor material and the metallic gate electrode; and a third layer comprising a substrate, wherein the first, second and third layers are arranged in order such that the second layer is positioned between the first layer and the third layer.

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